



2N7002

N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(ON)} max	I _D max T _A = 25°C		
60V	7.5Ω @ V _{GS} = 5V	210mA		

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Small Surface Mount Package
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Notes 3 & 4)
- Qualified to AEC-Q101 standards for High Reliability

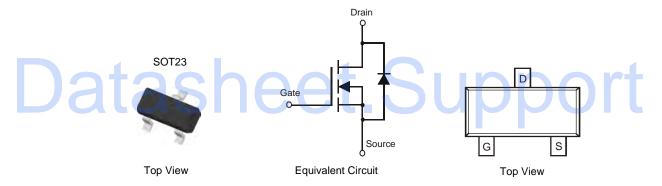
Description and Applications

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(on)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- Power Management Functions

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish annealed over Alloy 42 leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208 63
- Terminal Connections: See Diagram
- Weight: 0.008 grams (approximate)



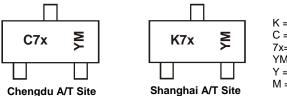
Ordering Information (Note 5)

Part Number	Qualification	Case	Packaging
2N7002-7-F	Commercial	SOT23	3,000/Tape & Reel
2N7002-13-F	Commercial	SOT23	10,000/Tape & Reel
2N7002Q-7-F	Automotive	SOT23	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Product manufactured with Date Code V12 (week 50, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V12 are built with Non-Green Molding Compound and may contain Halogens or Sb₂O₃ Fire Retardants.
- 5. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K = SAT (Shanghai Assembly/ Test site)C = CAT (Chengdu Assembly/ Test site)7x= Product Type Marking Code

7x= Product Type Marking Code YM = Date Code Marking

Y = Year (ex: N = 2002)

M = Month (ex: 9 = September)

Date Code Key

	,															
Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	N	Р	R	S	Т	J	V	W	X	Υ	Z	Α	В	С	D	Е
Month	Jan	l F	eb	Mar	Apr	l M	lav	Jun	Jul	Α	ug	Sep	Oct	N	ov	Dec
Code	1		2	3	4		5	6	7		8	9	0		N	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	60	V
Drain-Gate Voltage $R_{GS} \le 1.0 M\Omega$			V_{DGR}	60	V
Gate-Source Voltage		Continuous Pulsed	V_{GSS}	±20 ±40	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$ $T_A = 100^{\circ}C$	I _D	170 120 105	mA
Continuous Drain Current (Note 7) V _{GS} = 10V	Steady State	$T_A = 25^{\circ}C$ $T_A = 85^{\circ}C$ $T_A = 100^{\circ}C$	l _D	210 150 135	mA
Maximum Body Diode Forward Current (Note 7)	Pulsed Continuous		I _S	0.5 2	А
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	800	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units	
Total Power Dissipation	(Note 6)	ם	370	mW	
Total Fower Dissipation	(Note 7)	P_{D}	540		
Thermal Resistance, Junction to Ambient	(Note 6)	J	348		
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{ hetaJA}$	241	°C/W	
Thermal Resistance, Junction to Case	(Note 7)	$R_{\theta JC}$	91		
Operating and Storage Temperature Range		$T_{J_i}T_{STG}$	-55 to 150	°C	

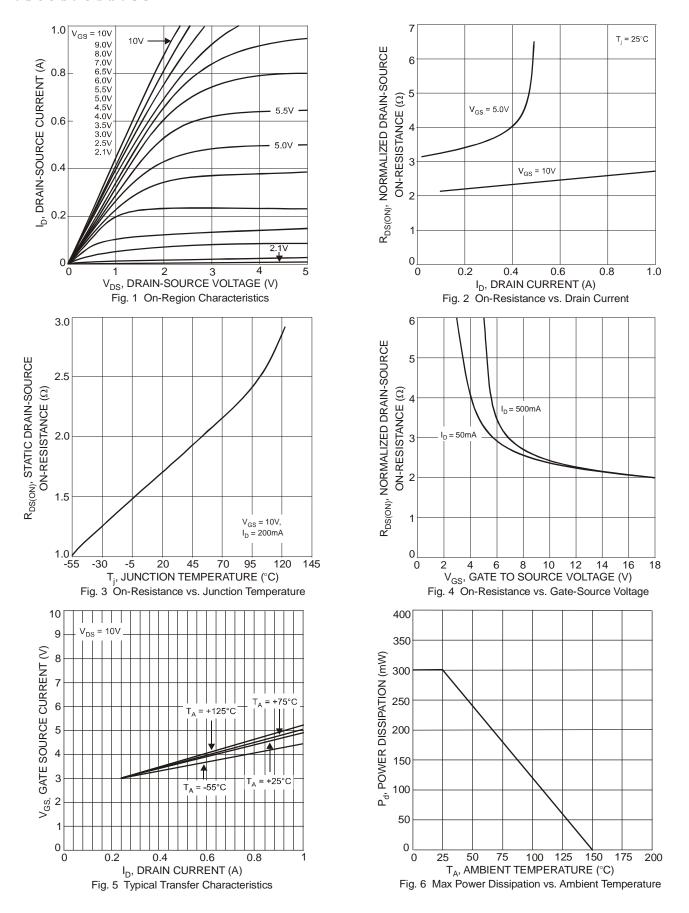
Electrical Characteristics @TA = 25°C unless otherwise specified

Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)								
Drain-Source Breakdown Voltage		BV _{DSS}	60	70	_	V	$V_{GS} = 0V, I_D = 10\mu A$	
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}	_	_	1.0 500	μΑ	$V_{DS} = 60V, V_{GS} = 0V$	
Gate-Body Leakage		I _{GSS}	_	_	±10	nA	$V_{GS} = \pm 20V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							_	
Gate Threshold Voltage		V _{GS(th)}	1.0	_	2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance	@ T_J = 25°C@ T_J = 125°C	R _{DS (ON)}	_	3.2 4.4	7.5 13.5	Ω	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$	
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	$V_{GS} = 10V, V_{DS} = 7.5V$	
Forward Transconductance		g _{FS}	80	_	_	mS	$V_{DS} = 10V, I_D = 0.2A$	
Diode Forward Voltage		V_{SD}	_	0.78	1.5	V	$V_{GS} = 0V, I_{S} = 115mA$	
DYNAMIC CHARACTERISTICS (Note 9)								
Input Capacitance		C _{iss}	_	22	50	pF	\/ O5\/\\	
Output Capacitance		Coss	_	11	25	pF	$V_{DS} = 25V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance		C _{rss}	_	2.0	5.0	pF	1 = 1.0IVII IZ	
Gate resistance		R_g	_	120	_	Ω	$V_{DS} = 0V, V_{GS} = 0V,$ f = 1.0MHz	
Total Gate Charge (V _{GS} = 4.5V)		Qg	_	223	_			
Gate-Source Charge			_	82	_	рC	$V_{DS} = 10V, I_D = 250mA$	
Gate-Drain Charge		Q_{gd}	_	178	_			
SWITCHING CHARACTERISTICS (Note 9)								
Turn-On Delay Time		t _{D(on)}	_	2.8	_		\/ 20\/ L 0.0A	
urn-On Rise Time		t _r	_	3.0	_	ns	$V_{DD} = 30V, I_D = 0.2A,$	
Turn-Off Delay Time		t _{D(off)}	_	7.6 —		115	$R_L = 150\Omega$, $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$	
Turn-Off Fall Time		t _f		5.6	_	TIGEN = 2322		

Notes:

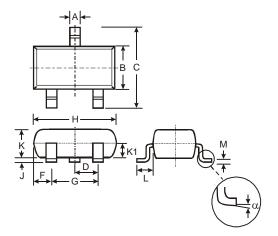
^{6.} Device mounted on FR-4 PCB, with minimum recommended pad layout
7. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.





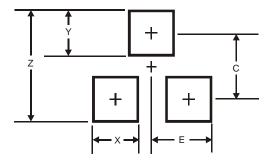


Package Outline Dimensions



SOT23								
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.903	1.10	1.00					
K1	-	-	0.400					
L	0.45	0.61	0.55					
M	0.085	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Υ	0.9
С	2.0
Е	1.35



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